



型号 : SLS5N60

N-CHANNEL MOSFET in a TO-252 Plastic Package.

主要特性/Features

低栅电荷,低反馈电容,开关速度快。

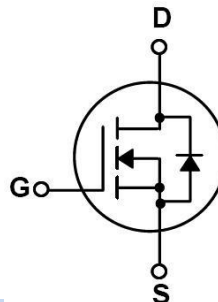
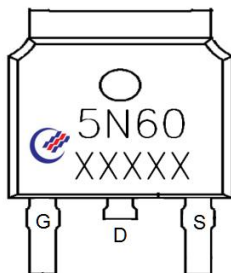
Low gate charge, low crss, fast switching.

应用/Application

用于高功率 DC/DC 转换和功率开关。

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

印字/MARKING 等效电路/Equivalent Circuit



极限参数/Absolute Maximum Ratings(TA=25°C unless otherwise noted)

参数Parameter	符号Symbol	数值Value	单位Unit
Drain-Source Voltage	V_{DSS}	600	V
Drain Current	$I_D(T_C=25^\circ\text{C})$	5.0	A
Drain Current	$I_D(T_C=100^\circ\text{C})$	3.1	A
Drain Current - Pulsed	I_{DM}	20	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	242	mJ
Power Dissipation	$P_D(T_C=25^\circ\text{C})$	40	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

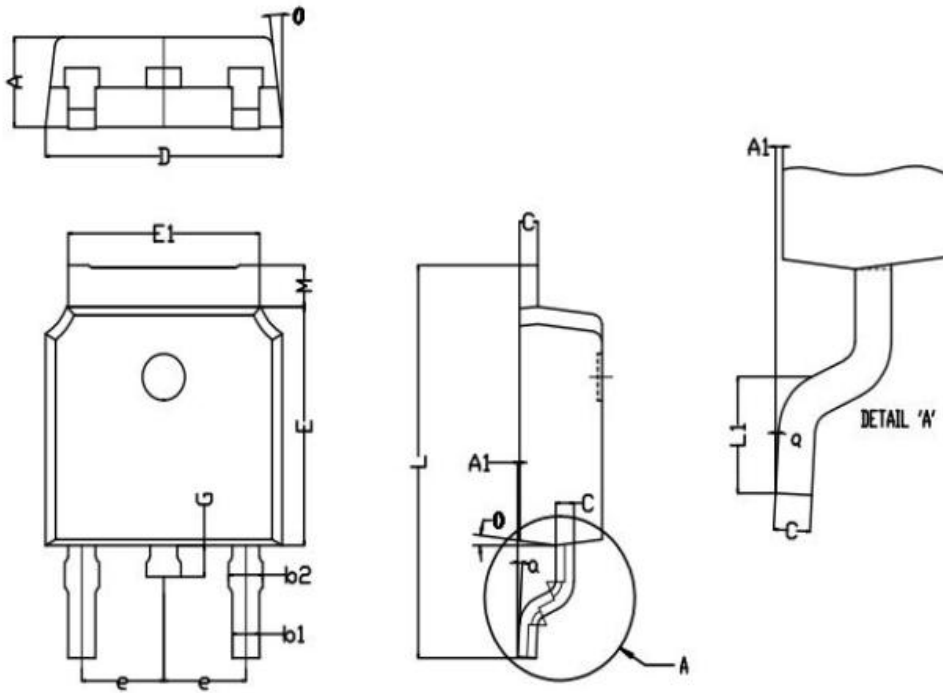


电性能参数/Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BVDSS	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	600	-	-	V
RDS(ON)	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=1A$	-	-	2.5	Ω
VGS(th)	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5	3.5	4.5	V
IDSS	Drain-Source Leakage Current	$V_{DS}=600V, V_{GS}=0V$	-	-	1	μA
IGSS	Gate Leakage Current, Forward	$V_{GS}=\pm 30V, V_{DS}=0V$	-	-	± 100	Na
VSD	Drain-Source Diode Forward Voltage	$V_{GS}=0V, I_S=1.0A$	-	-	1.4	V
TJ, TSTG	Operating and Storage Temperature	-55 to 150°C Max				



成品外观尺寸/T0252-2L Package Information



Symbol	Dim in mm		
	Min	Nor	Max
A	2.25	2.30	2.35
L1	2.90	3.00	3.10
b1	0.71	0.76	0.81
b2	0.91	0.96	1.01
C	0.46	0.51	0.56
D	6.55	6.60	6.65
e	2.29 (BSC)		
E	6.05	6.10	6.15
E1	5.23	5.33	5.43
L	9.84	10.04	10.24
A1	0.00	0.05	0.10
M	1.01	1.06	1.11
G	0.70	0.80	0.90
0	0°	5°	10°
Q	0°	3°	6°